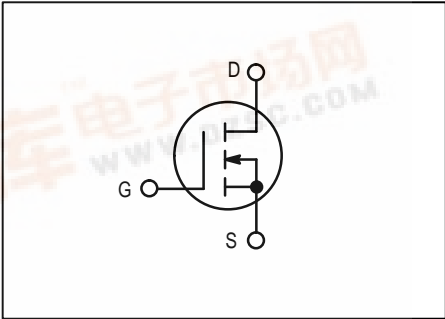
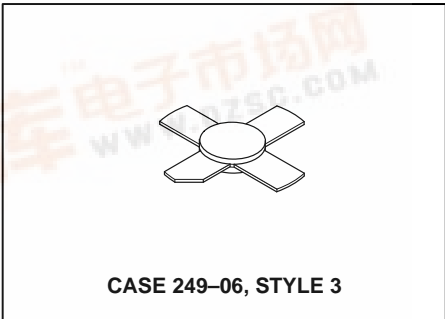
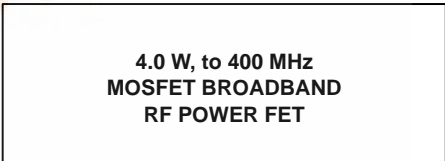


The RF MOSFET Line  
**Power Field Effect Transistor**  
**N-Channel Enhancement-Mode MOSFET**

Designed primarily for wideband large-signal output and driver from 30–500 MHz.

- Typical Performance at 400 MHz, 28 Vdc  
 Output Power = 4.0 Watts  
 Gain = 17 dB  
 Efficiency = 50%
- Excellent Thermal Stability, Ideally Suited for Class A Operation
- Facilitates Manual Gain Control, ALC and Modulation Techniques
- 100% Tested for Load Mismatch at All Phase Angles with 30:1 VSWR
- Low  $C_{RSS}$  – 0.8 pF Typical at  $V_{DS} = 28$  Volts



**MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Gate Voltage	$V_{DSS}$	65	Vdc
Drain-Gate Voltage ( $R_{GS} = 1.0 \text{ M}\Omega$ )	$V_{DGR}$	65	Vdc
Gate-Source Voltage	$V_{GS}$	$\pm 40$	Vdc
Drain Current-Continuous	$I_D$	1.0	ADC
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	24 0.14	Watts W/ $^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	200	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Thermal Resistance — Junction to Case	$R_{\theta JC}$	7.2	$^\circ\text{C}/\text{W}$
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NOTE: Handling and Packaging — MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.



**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**OFF CHARACTERISTICS**

Drain–Source Breakdown Voltage ( $V_{DS} = 0\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ , $I_D = 5.0\text{ mA}$ )	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ V}$ )	$I_{DSS}$	—	—	0.8	mA
Gate–Source Leakage Current ( $V_{GS} = 40\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	1.0	$\mu\text{A}$

**ON CHARACTERISTICS**

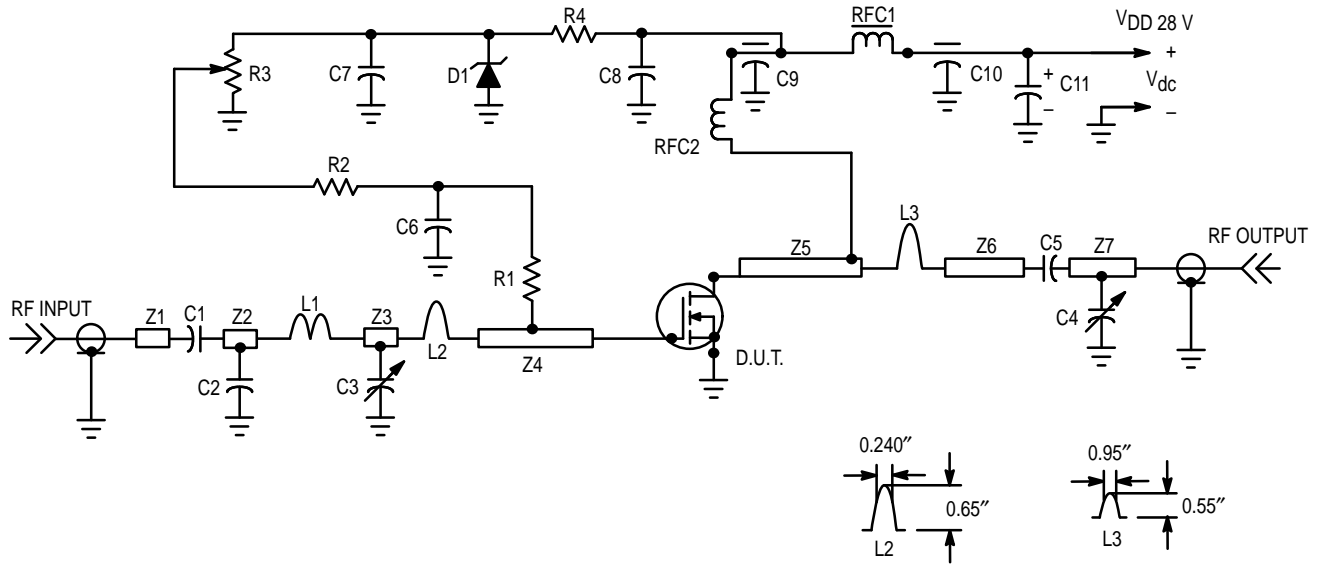
Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 10\text{ mA}$ )	$V_{GS(th)}$	1.0	3.0	6.0	Vdc
Drain Source On–Voltage ( $V_{DS(on)}$ , $V_{GS} = 10\text{ Vdc}$ , $I_D = 500\text{ mA}$ )	$V_{DS(on)}$	—	3.8	—	Vdc
Forward Transconductance ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 250\text{ mA}$ )	$g_{fs}$	110	160	—	mS

**DYNAMIC CHARACTERISTICS**

Input Capacitance ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{iss}$	—	6.0	—	pF
Output Capacitance ( $V_{DS} = 28\text{ V}$ , $V_{GS} = 0\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$C_{oss}$	—	8.0	—	pF
Reverse Transfer Capacitance ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$C_{rss}$	—	0.8	—	pF

**FUNCTIONAL CHARACTERISTICS**

Common Source Power Gain ( $V_{DD} = 28\text{ Vdc}$ , $P_{out} = 4.0\text{ W}$ , $f = 400\text{ MHz}$ , $I_{DQ} = 50\text{ mA}$ )	$G_{ps}$	15	17	—	dB
Drain Efficiency ( $V_{DD} = 28\text{ Vdc}$ , $P_{out} = 4.0\text{ W}$ , $f = 400\text{ MHz}$ , $I_{DQ} = 50\text{ mA}$ )	$\eta$	45	50	—	%
Electrical Ruggedness ( $V_{DD} = 28\text{ Vdc}$ , $P_{out} = 4.0\text{ W}$ , $f = 400\text{ MHz}$ , $I_{DQ} = 50\text{ mA}$ ) Load VSWR = 30:1 at All Phase Angles at Frequency of Test	$\psi$	No Degradation in Output Power			
Series Equivalent Input Impedance ( $V_{DD} = 28\text{ Vdc}$ , $P_{out} = 4.0\text{ W}$ , $f = 400\text{ MHz}$ , $I_{DQ} = 50\text{ mA}$ )	$Z_{in}$	—	$5.23-j\ 27.2$	—	Ohms
Series Equivalent Output Impedance ( $V_{DD} = 28\text{ Vdc}$ , $P_{out} = 4.0\text{ W}$ , $f = 400\text{ MHz}$ , $I_{DQ} = 50\text{ mA}$ )	$Z_{out}$	—	$14.7-j\ 31.2$	—	Ohms



C1, C5	220 pF, Chip Capacitor	R3	10 k $\Omega$ , 10 Turns Bourns
C2	18 pF, ATC Chip Capacitor	R4	1.8 k $\Omega$ , 1/4 Watt
C3	2.0–20 pF, Johanson Trimmer Capacitor	RFC1	Ferroxcube VK200–19/4B
C4	2.0–10 pF, Johanson Trimmer Capacitor	RFC2	10 Turns, #20 AWG, Enameled Close Wound, 0.250" ID
C6, C7, C8	0.1 $\mu$ F	Z1	Microstrip Line 0.167" wide, 0.820" long
C9, C10	680 pF, Feed Through	Z2	Microstrip Line 0.240" wide, 0.240" long
C11	50 $\mu$ F, 50 V	Z3	Microstrip Line 0.240" wide, 0.240" long
L1	#20 AWG, 1 Turn 0.255" ID	Z4	Microstrip Line 0.230" wide, 0.590" long
L2	#20 AWG, Hairpin 1.3" long, bend into hairpin	Z5	Microstrip Line 0.230" wide, 0.580" long
L3	#20 AWG, Hairpin 1.1" long, bend into hairpin	Z6	Microstrip Line 0.167" wide, 0.620" long
R1	160 $\Omega$ , 1/2 Watt	Z7	Microstrip Line 0.167" wide, 0.800" long
R2	10 k $\Omega$ , 1/2 Watt		

Board Material 0.060" Glass Teflon<sup>®</sup> 2 oz. Copper clad both sides  $\epsilon_r = 2.55$

**Figure 1. 400 MHz Test Circuit**

## Typical Characteristics

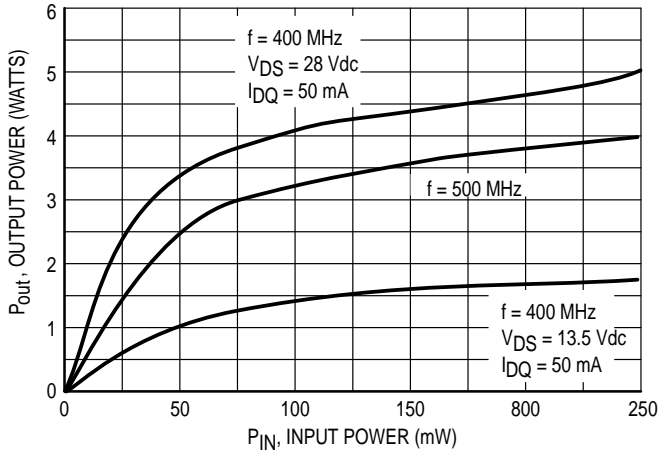


Figure 2. Output Power versus Input Power

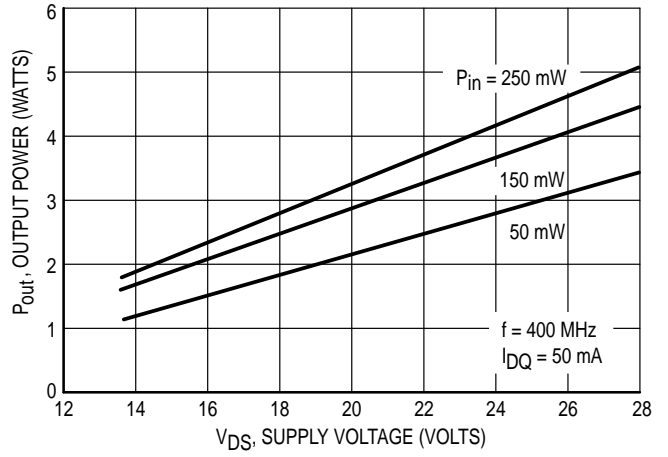


Figure 3. Output Power versus Voltage

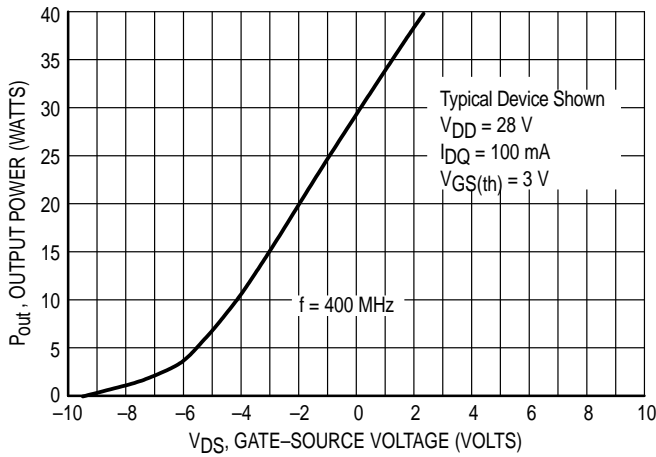


Figure 4. Output Power versus Gate Voltage

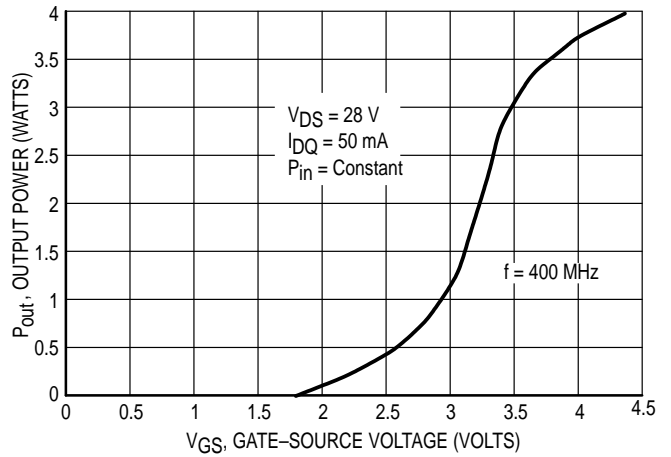


Figure 5. Output Power versus Gate Voltage

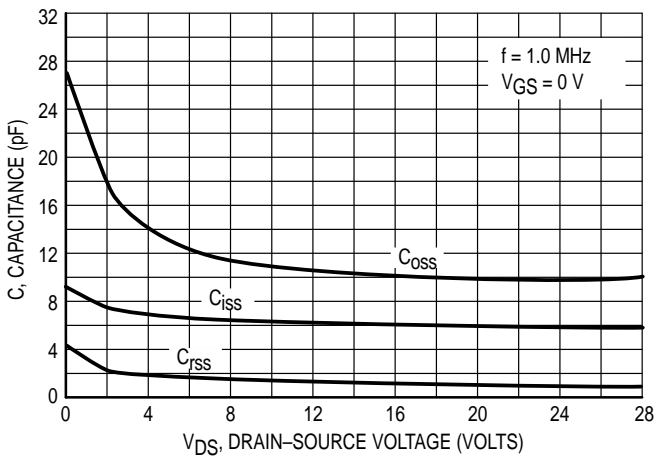


Figure 6. Capacitance versus Drain-Source Voltage

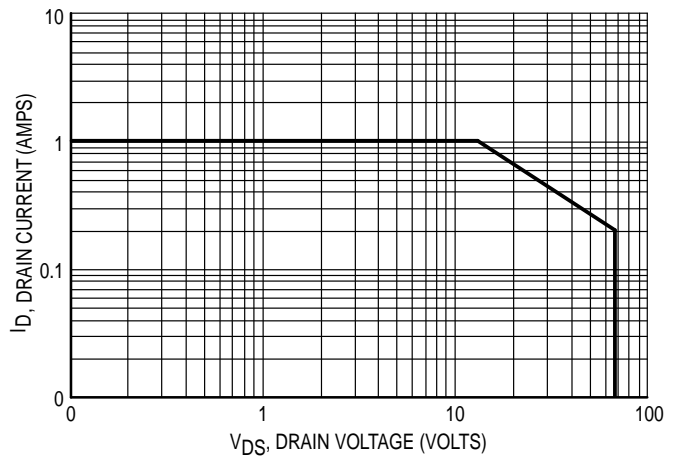


Figure 7. DC Safe Operating Area

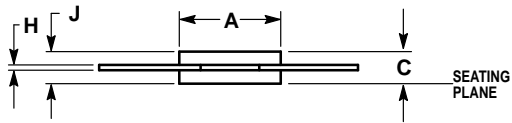
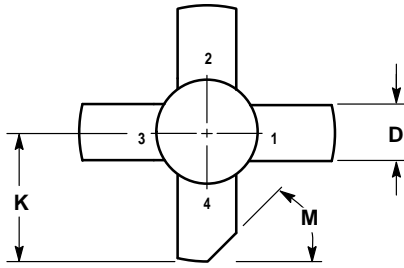
f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	S <sub>11</sub>	∠φ	S <sub>21</sub>	∠φ	S <sub>12</sub>	∠φ	S <sub>22</sub>	∠φ
10	0.96	-2.0	14.47	177	0.01	96	1.11	-5.0
30	0.99	-16	13.34	169	0.02	79	0.92	-11
50	0.97	-28	12.96	159	0.03	70	0.90	-22
75	0.94	-40	12.24	148	0.04	60	0.87	-35
100	0.90	-52	11.40	139	0.05	51	0.84	-45
120	0.87	-61	10.70	132	0.05	45	0.81	-53
150	0.83	-72	9.66	123	0.06	37	0.77	-63
170	0.81	-79	9.05	118	0.06	33	0.75	-69
200	0.78	-88	8.21	110	0.06	26	0.72	-77
220	0.77	-93	7.67	106	0.07	23	0.71	-81
250	0.75	-100	7.00	100	0.07	18	0.69	-87
300	0.72	-110	6.00	92	0.07	12	0.67	-96
350	0.71	-118	5.24	84	0.07	6.0	0.66	-103
390	0.71	-124	4.73	79	0.07	1.0	0.66	-108
400	0.70	-125	4.63	77	0.07	0	0.67	-109
410	0.70	-127	4.52	76	0.07	-1.0	0.66	-110
450	0.70	-131	4.10	71	0.07	-5.0	0.66	-114
470	0.70	-133	3.93	69	0.06	-6.0	0.67	-116
500	0.70	-137	3.68	65	0.06	-8.0	0.67	-118
600	0.71	-145	3.01	55	0.06	-14	0.69	-126
700	0.72	-153	2.51	46	0.05	-18	0.71	-132
800	0.73	-160	2.13	37	0.04	-21	0.73	-137
900	0.75	-166	1.83	30	0.03	-19	0.75	-142
1000	0.76	-171	1.60	23	0.03	-10	0.77	-146
1100	0.77	-177	1.40	16	0.02	3.0	0.79	-151
1200	0.78	177	1.25	10	0.02	18	0.80	-155
1300	0.79	172	1.11	4.0	0.03	29	0.82	-159
1400	0.81	166	1.00	-1.0	0.03	35	0.83	-163
1500	0.81	161	0.90	-6.0	0.03	48	0.85	-166

**Table 1. Common Source Scattering Parameters** ( $V_{DS} = 28$  Vdc,  $I_D = 200$  mA,  $50 \Omega$  System)

f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	S <sub>11</sub>	∠φ	S <sub>21</sub>	∠φ	S <sub>12</sub>	∠φ	S <sub>22</sub>	∠φ
10	0.96	-4.0	16.09	176	0.01	85	1.08	-8.0
20	1.00	-15	14.82	171	0.02	82	0.88	-10
30	0.98	-23	14.64	164	0.03	73	0.89	-20
50	0.94	-39	13.76	152	0.04	63	0.86	-38
85	0.86	-61	11.81	134	0.06	47	0.79	-61
150	0.73	-91	8.63	112	0.08	27	0.70	-91
170	0.71	-97	7.90	107	0.09	23	0.68	-98
200	0.68	-106	6.97	101	0.09	17	0.67	-106
210	0.68	-109	6.68	99	0.09	15	0.66	-108
250	0.66	-117	5.75	92	0.09	10	0.65	-116
300	0.64	-126	4.85	84	0.09	4.0	0.64	-124
350	0.64	-133	4.18	78	0.09	-1.0	0.64	-129
390	0.64	-137	3.75	73	0.09	-5.0	0.65	-133
400	0.64	-138	3.66	71	0.09	-6.0	0.65	-134
410	0.64	-140	3.57	70	0.09	-7.0	0.65	-135
450	0.64	-143	3.23	66	0.08	-10	0.66	-138
470	0.65	-145	3.08	64	0.08	-11	0.66	-139
500	0.65	-147	2.88	61	0.08	-13	0.67	-141
550	0.66	-151	2.59	56	0.08	-16	0.67	-144
600	0.67	-154	2.35	52	0.07	-18	0.68	-146
700	0.69	-160	1.96	43	0.07	-22	0.71	-150
800	0.70	-166	1.67	35	0.06	-25	0.73	-154
900	0.72	-171	1.43	28	0.05	-24	0.75	-158
1000	0.74	-177	1.26	22	0.04	-21	0.77	-161
1100	0.74	178	1.11	16	0.04	-14	0.78	-164
1200	0.76	173	0.99	10	0.04	-6.0	0.80	-168
1300	0.78	168	0.88	5.0	0.04	2.0	0.81	-171
1400	0.79	163	0.80	0	0.03	8.0	0.83	-174
1500	0.80	158	0.72	-5.0	0.03	19	0.84	-177

**Table 2. Common Source Scattering Parameters ( $V_{DS} = 12.5$  Vdc,  $I_D = 200$  mA,  $50 \Omega$  System)**

## PACKAGE DIMENSIONS



**NOTES:**


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. SEATING PLANE = GROUND AND IS CONNECTED TO PIN 1 AND 3.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.271	0.286	6.88	7.26
C	0.112	0.136	2.84	3.45
D	0.215	0.235	5.46	5.97
H	0.055	0.065	1.40	1.65
J	0.003	0.007	0.08	0.18
K	0.435	—	11.05	—
M	45° REF		45° REF	

**STYLE 3:**

- PIN 1. SOURCE
2. GATE
3. SOURCE
4. DRAIN

**CASE 249-06  
ISSUE H**

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